Product data sheet

1. General description

Dual ultrafast power diode in a SOT78 (TO-220AB) plastic package

2. Features and benefits

- Ultra low leakage current
- High junction temperature up to 175 °C
- Low on-state loss
- Fast switching
- Soft recovery characteristic minimizes power consuming oscillations
- High reverse surge capability
- High thermal cycling performance
- Low thermal resistance

3. Applications

Home appliance power supply

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage			-	-	200	V
I _{O(AV)}	average output current	δ = 0.5; T _{mb} ≤ 149 °C; Square-ware pulse		-	-	20	А
I _{FSM}	non-repetitive peak forward current	$T_{j(init)}$ = 25 °C; t_p = 8.3 ms; SIN; per diode; Fig. 4		-	-	137	А
I _{RRM}	repetitive peak reverse current	t_p = 2 μ s; δ = 0.001; per diode		-	-	0.2	А
V_{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 k Ω ; all pins		-	-	8	kV
Dynamic char	acteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/µs}$; $T_j = 25 \text{ °C}$; Fig. 7		-	18	25	ns
Static charact	eristics		•				
V _F	forward voltage	I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>		-	0.76	0.85	V





5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	A1 A2
2	K	cathode	 	K K
3	A2	anode 2	TO-220AB (SOT78)	sym125

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BYV32E-200P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

Type number	Marking code
BYV32E-200P	BYV32E-200P

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	200	V
V_{RWM}	crest working reverse voltage		-	200	V
V _R	reverse voltage	DC	-	200	V
I _{F(AV)}	average forward current	\bar{o} = 0.5; $T_{mb} \le$ 149 °C; Square-ware pulse; Fig. 1; Fig. 2; Fig. 3	-	10	A
I _{O(AV)}	average output current	\bar{o} = 0.5; T _{mb} ≤ 149 °C; Square-ware pulse	-	20	A
I _{FSM}	non-repetitive peak forward current	SIN; $t_p = 10 \text{ ms}$; $T_{j(init)} = 25 \text{ °C}$; per diode; Fig. 4	-	125	A
		SIN; t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; per diode; Fig. 4	-	137	A
I _{RRM}	repetitive peak reverse current	δ = 0.001; t_p = 2 μ s; per diode	-	0.2	Α
I _{RSM}	non-repetitive peak reverse current	t _p = 100 μs; per diode	-	0.2	A
T _{stg}	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C
V _{ESD}	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ; all pins	-	8	kV

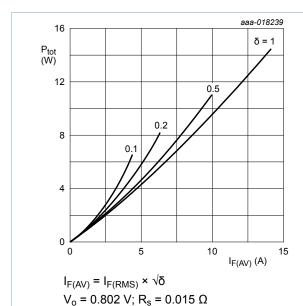


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

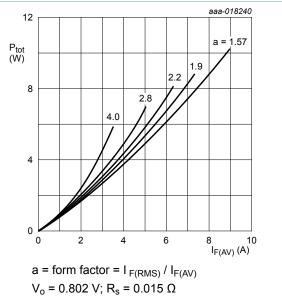


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

BYV32E-200P

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Dual ultrafast power diode

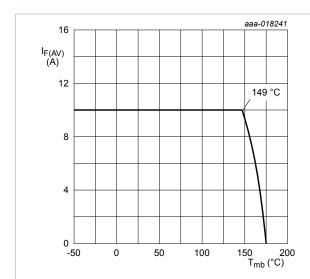


Fig. 3. Forward current as a function of mounting base temperature; maximum values

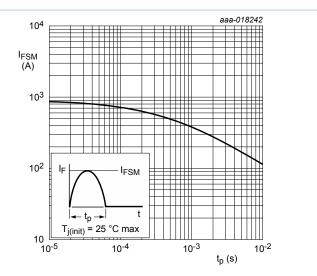


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance from junction to mounting base	from junction to	with heatsink compound; both diodes conducting	-	-	1.4	K/W
	with heatsink compound; per diode; Fig. 5	-	-	2.4	K/W	
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	_	60	-	K/W

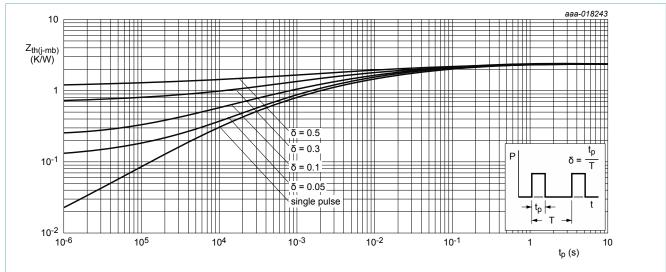
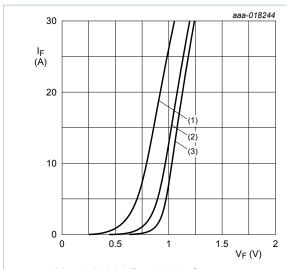


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics					
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	13.5	-	nC
		$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	14.5	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7	-	18	25	ns
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$	-	1.7	-	A
Static char	acteristics					
V _F	forward voltage	I _F = 20 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.06	1.15	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>	-	0.76	0.85	V
		I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	0.95	-	V
I _R	reverse current	V _R = 200 V; T _j = 25 °C	-	0.3	5	μΑ
		V _R = 200 V; T _j = 150 °C	-	70	250	μA



 V_o = 0.802 V; R_s = 0.015 Ω

(1) T_i = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) T_j = 25 °C; maximum values

Fig. 6. Forward current as a function of forward voltage

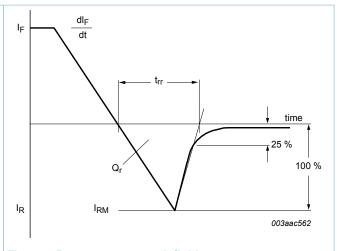
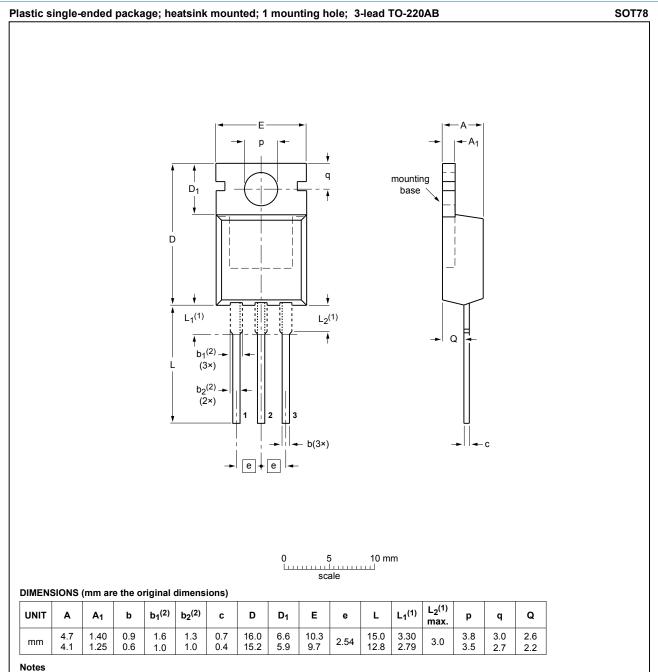


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



- 1. Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN ISSUE DAT	
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 8. Package outline TO-220AB (SOT78)

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Dual ultrafast power diode

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